IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

plicant: Kie Y. Ahn et al.

Examiner:

David S. Blum

Serial No.:

09/945,535

Group Art Unit:

2813

Filed:

August 30, 2001

Docket:

1303.026US1

Title: HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO2

<u>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT</u>

MS RCE Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Supplemental Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Supplemental Information Disclosure Statement considered.

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Serial No :09/945,535

Filing Date: August 30, 2001

Title: HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO2

Page 2 Dkt: 1303.026US1

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Pursuant to 37 C.F.R. 1.98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications are no longer required to be provided to the Office. Notification of this change was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004. Thus, Applicant has not included copies of any US Patents or Published Applications cited with this submission. Should the Office require copies to be provided, Applicant respectfully requests that notice of such requirement be directed to Applicant's below-signed representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A. P.O. Box 2938
Minneapolis, MN 55402
508-865-8211

Date 2/09/05

David Suhl

Reg. No. 43,169

CHUH U

Signature Lee

PTO/SB/08A(10-01)
Approved for use through 10/31/2002. OMB 651-0031
US Patient & Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number Substitute for form 1449A/PTO omplete if Known INFORMATION DISCLOSURE 09/945,535 **Application Number** TATEMENT BY APPLICANT **Filing Date** August 30, 2001 s as necessary) Ahn, Kie **First Named Inventor** 2813 **Group Art Unit** Blum, David **Examiner Name** Attorney Docket No: 1303.026US1

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S/N 09/945,535 PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Kie Y. Ahn et al.

Examiner: David S. Blum

Serial No.:

09/945,535

Group Art Unit: 2813

Filed:

August 30, 2001

Docket: 1303.026US1

Title:

HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZRO2

COMMUNICATION CONCERNING RELATED APPLICATION(S)

Mail Stop RCE Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

Serial/Patent No. 11/036296	Filing Date January 14, 2005	Attorney Docket 1303.030US2	Title LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO3 GATE DIELECTRICS
10/930138	August 31, 2004	1303.044US2	EVAPORATION OF Y-Si-O FILMS FOR MEDIUM-k DIELETRICS
10/930184	August 31, 2004	1303.021US2	CRYSTALLINE OR AMORPHOUS MEDIUM-K GATE OXIDES, Y2O3 AND GD203
10/930516	August 31, 2004	1303.078US2	ATOMIC LAYER DEPOSITED HISION DIELECTRIC FILMS
10/931341	August 31, 2004	1303.082US2	ATOMIC LAYER DEPOSITED ZR-SN- TI-O FILMS USING TiI4
10/930431	August 31, 2004	1303.056US2	ATOMIC LAYER-DEPOSITED HfAIO3 FILMS FOR GATE DIELECTRICS
10/931365	August 31, 2004	1303.059US2	Pr2O3-BASED La-oxide GATE DIELECTRICS
10/931364	August 31, 2004	1303.069US2	LANTHANIDE DOPED TiOx DIELECTRIC FILMS BY PLASMA OXIDATION

COMMUNICATION CONCERNING RELATED APPLICATIONS

Scrial Number: 09/945,535

Filing Date: August 30, 2001

Tide: HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZRO2

Page 2 Dkt: 1303.026US1

10/931343	August 31, 2004	1303.101US2	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS
10/931340	August 31, 2004	1303.107US2	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS
10/931356	August 31, 2004	1303.026US2	HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO2
11/031289	January 7, 2005	1303.069US3	LANTHANIDE DOPED TiOx DIELECTRIC FILMS BY PLASMA OXIDATION

Respectfully submitted,

KIE Y. AHN ET AL.

By Applicants' Representatives,

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Minneapolis, MN 55402

508-865-8211

Date 2/09/05

David Cub

Reg. No. 43,169

Signature

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Application Number	09/945535
Filing Date	August 30, 2001
First Named Inventor	Ahn, Kie
Group Art Unit	2813
Examiner Name	Blum, David

Attorney Docket No: 1303.026US1

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Approved for use through 10/31/2002. OMB 551-0031
US Patent & Trademark Office: U.S. DEPARTMENT OF COMMERCE
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number. Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE 09/945535 **Application Number** STATEMENT BY APPLICANT August 30, 2001 **Filing Date** (Use as many sheets as necessary) COPY **First Named Inventor** Ahn, Kie **Group Art Unit** 2813 Blum, David **Examiner Name** Attorney Docket No: 1303.026US1 Sheet 2 of 3

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Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
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Complete if Known Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE **Application Number** 09/945535 STATEMENT BY APPLICANT COPI August 30, 2001 (Use as many sheets as necessary) Filing Date Ahn, Kie **First Named Inventor Group Art Unit** 2813 Blum, David **Examiner Name** Attorney Docket No: 1303.026US1 Sheet 3 of 3

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First Named Inventor	Ahn, Kie
Group Art Unit	2813
Examiner Name	Blum, David

Sheet 1 of 8

Attorney Docket No: 1303.026US1

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EXAMINER

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	Group Art Unit	2813
	Examiner Name	Blum, David
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Application Number	09/945,535
Filing Date	August 30, 2001
First Named Inventor	Ahn, Kie
Group Art Unit	2813
Examiner Name	Blum, David

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First Named Inventor	Ahn, Kie	
Group Art Unit	2813	
Examiner Name	Blum, David	

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